

EVVOSEMI[®]

THINK CHANGE DO



ESD



TVS



MOS



LDO



Diode



Sensor



DC-DC

Product Specification

▶ Domestic	Part Number	IRFB4321
▶ Overseas	Part Number	IRFB4321
▶ Equivalent	Part Number	IRFB4321

EV is the abbreviation of name EVVO

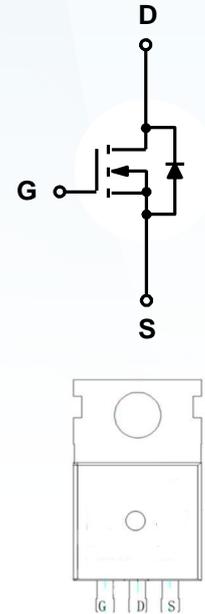
Features

- 150V,80A
 $R_{DS(ON)} < 12m\Omega @ V_{GS}=10V$ TYP:10.7 mΩ
 $R_{DS(ON)} < 15m\Omega @ V_{GS}=6V$ TYP:11.8mΩ

- Surface-mounted package
- Super Trench

Applications

- LCD TV appliances
- LCDM appliances
- High power inverter system



ABSOLUTE MAXIMUM RATINGS (T_J=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	150	V
Gate-Source Voltage	V _{GS}	±25	V
Continuous Drain Current (T _C =25°C) ^(1,3)	I _D	80	A
Continuous Drain Current (T _C =100°C) ^(1,3)	I _D	46	A
Pulsed Drain Current ^(1,2,3)	I _{DM}	240	A
Single Pulsed Avalanche Energy (V _{DD} =50V, L=1.0mH)	E _{AS}	684	mJ
Drain Power Dissipation	P _D	156	W
Thermal Resistance from Junction to Case ⁽²⁾	R _{θJC}	0.8	°C/W
Thermal Resistance- Junction to Ambient ⁽²⁾	R _{θJA}	62.5	°C/W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{STG}	-55~ +150	°C

Notes:

1. Pulse width ≤ 300 μs, duty cycle ≤ 2 %
2. Surface Mounted on minimum footprint pad area.
3. Limited by bonding wire

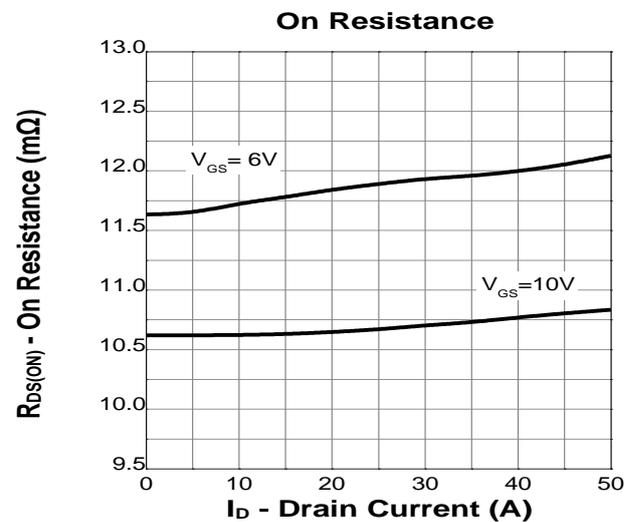
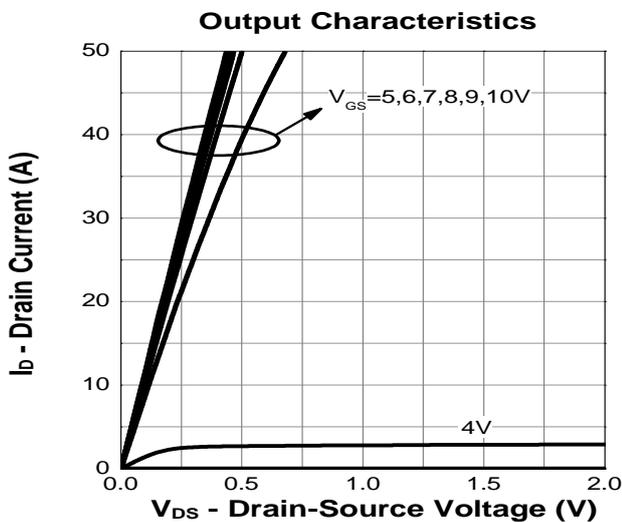
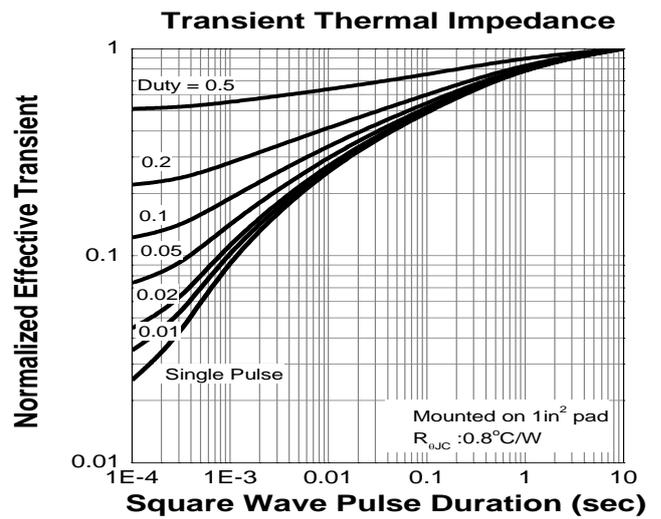
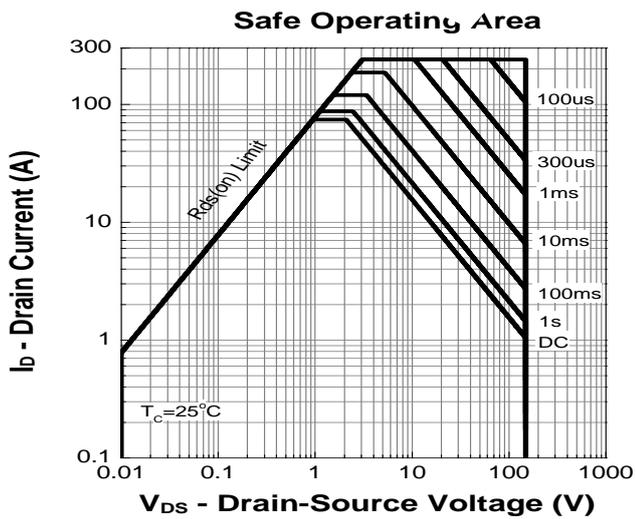
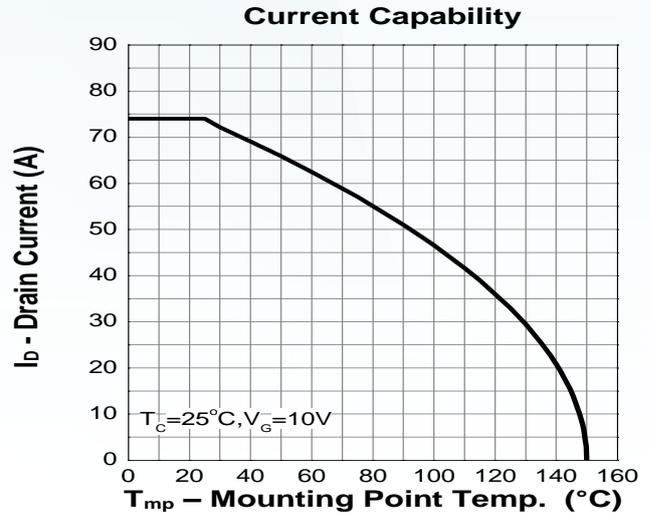
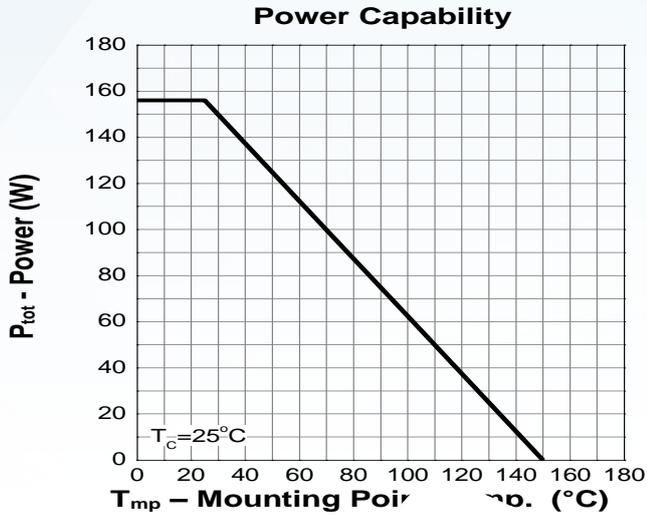
MOSFET ELECTRICAL CHARACTERISTICS(T_J=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D =250μA	100	-	-	V
Zero gate voltage drain current	I _{DSS}	V _{DS} =120V, V _{GS} = 0V	-	-	1	μA
Gate-body leakage current	I _{GSS}	V _{GS} = ±25V, V _{DS} = 0V	-	-	±100	nA
Gate threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	2.0	-	4.0	V
Drain-source on-resistance ^(a)	R _{DS(on)}	V _{GS} =10V, I _D =30A	-	10.7	12	mΩ
		V _{GS} =6V, I _D =20A	-	11.8	15	mΩ
Dynamic characteristics						
Input Capacitance	C _{iss}	V _{DS} =75V, V _{GS} =0V, f =1.0MHz	-	4756	-	pF
Output Capacitance	C _{oss}		-	318	-	
Reverse Transfer Capacitance	C _{rss}		-	65	-	
Switching characteristics						
Turn-on delay time	t _{d(on)}	V _{DD} =75V, I _D =30A, R _G =3.9Ω, V _{GS} =10V	-	19	-	ns
Turn-on rise time	t _r		-	69	-	
Turn-off delay time	t _{d(off)}		-	55	-	
Turn-off fall time	t _f		-	80	-	
Total Gate Charge	Q _g	V _{DS} =75V, I _D =30A, V _{GS} =10V	-	81	-	nC
Gate-Source Charge	Q _{gs}		-	21	-	
Gate-Drain Charge	Q _{gd}		-	17	-	
Source-Drain Diode characteristics						
Diode Forward voltage ^(a)	V _{SD}	T _C =25°C, V _{GS} =0V, I _S =30A	-	-	1.3	V
Diode Forward current	I _S	T _C =25°C	-	-	80	A
Body Diode Reverse Recovery Time	t _{rr}	T _C =25°C, I _F =30A, di/dt=100A/us		96		ns
Body Diode Reverse Recovery Charge	Q _{rr}	T _C =25°C, I _F =30A, di/dt=100A/us		355		nc

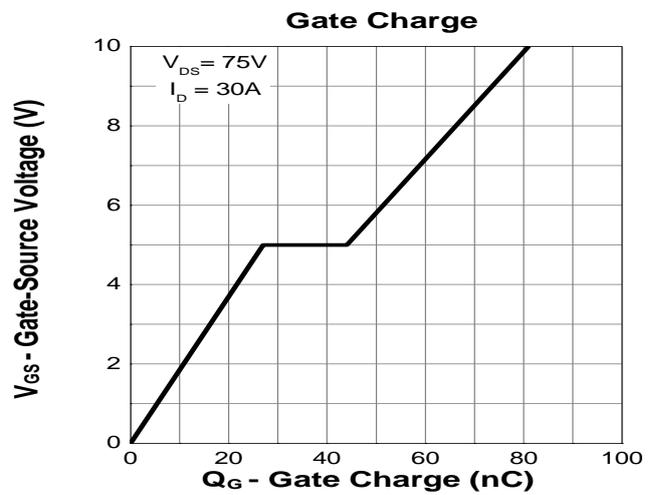
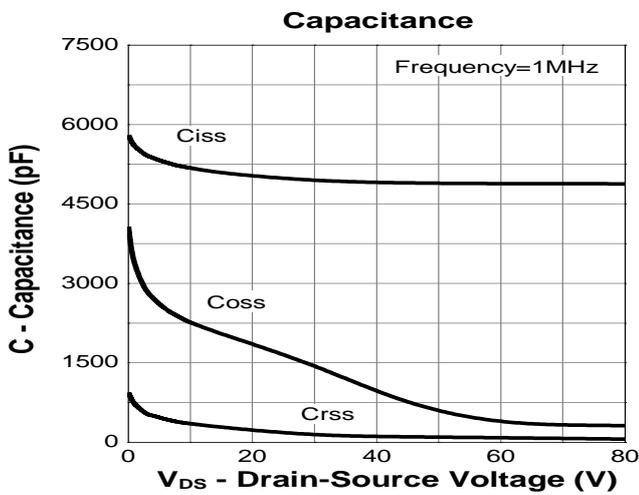
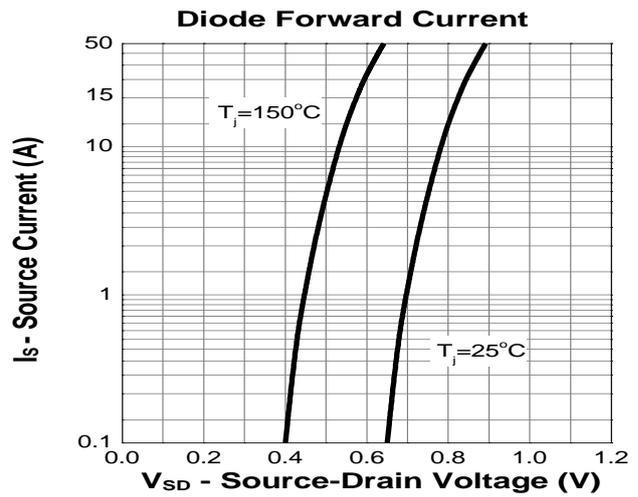
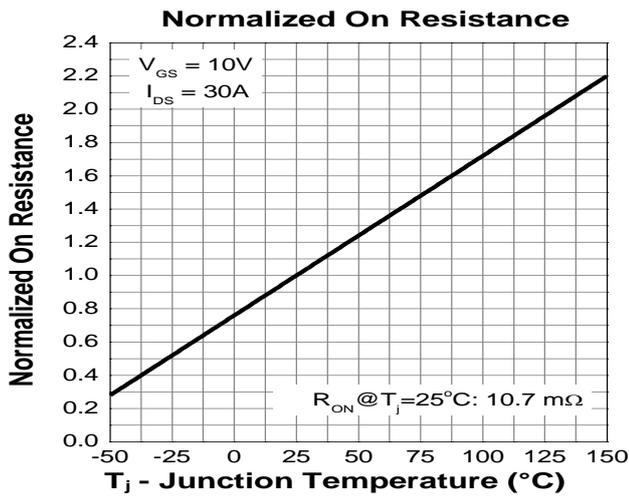
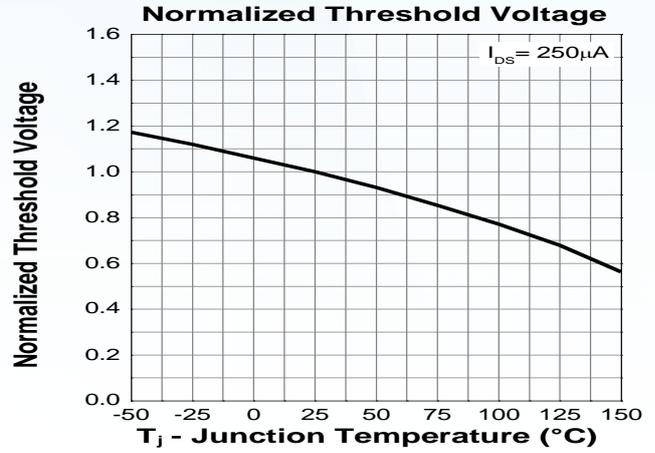
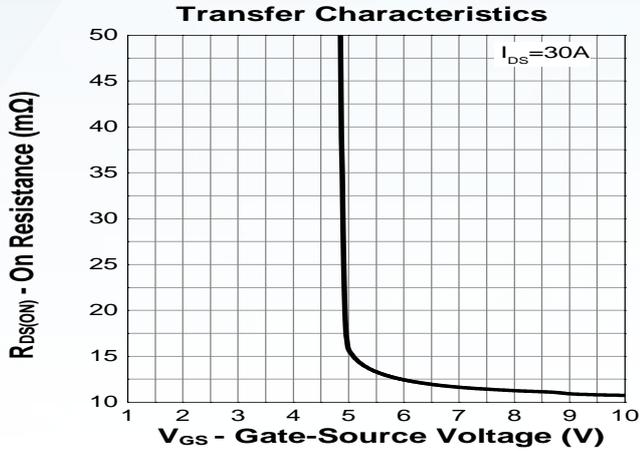
Notes:

- a) : Pulse test ; pulse width ≤ 300 μs, duty cycle ≤ 2%
 b) : Guaranteed by design, not subject to production testing

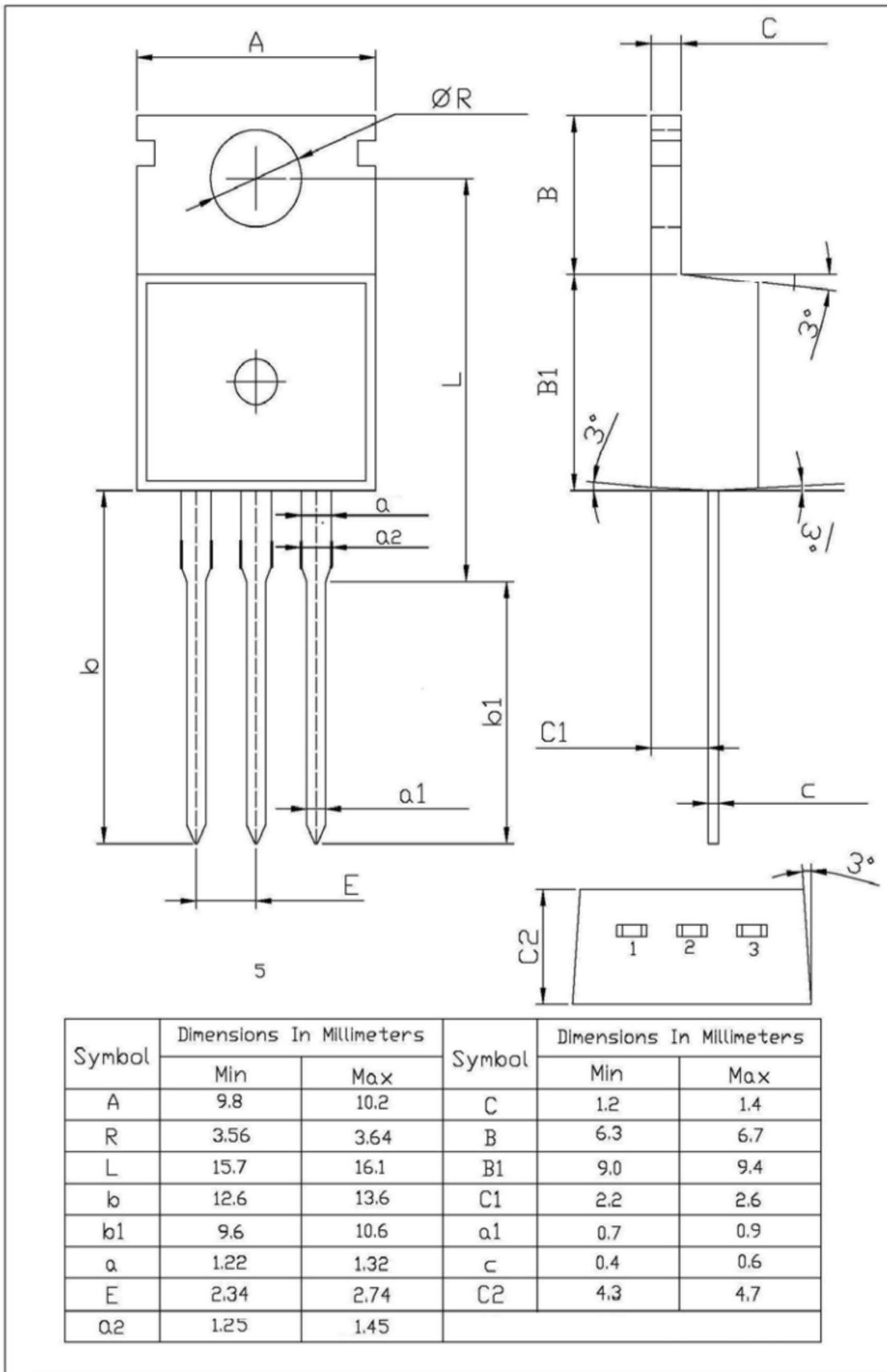
Typical Characteristics (cont.)



Typical Characteristics (cont.)



TO220 Package Information



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